



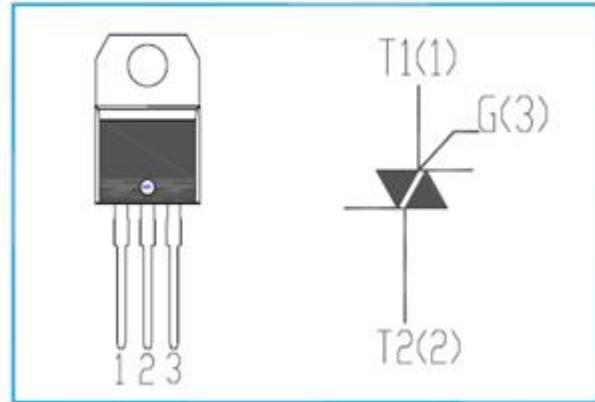
INCHANGE Semiconductor

isc Triacs

BT138-600E

FEATURES

- With TO-220 package
- Glass passivated triacs in a plastic envelope, Intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all our quadrants.
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**ABSOLUTE MAXIMUM RATINGS(Ta=25°C)**

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	600	V
V_{RRM}	Repetitive peak off-state voltage	600	V
$I_{T(RMS)}$	RMS on-state current (full sine wave)	12	A
I_{TSM}	Non-repetitive peak on-state current	95	A
P_{GM}	Peak gate power dissipation	5	W
$P_{G(AV)}$	Average gate power dissipation	0.5	W
T_j	Operating junction temperature	125	°C
T_{stg}	Storage temperature	-45~150	°C

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	$V_R=V_{RRM}$, $V_R=V_{RRM}$, $T_j=125^\circ\text{C}$	0.02 0.5		mA
I_{DRM}	Repetitive peak off-state current	$V_D=V_{DRM}$, $V_D=V_{DRM}$, $T_j=125^\circ\text{C}$	0.02 0.5		mA
I_{GT}	Gate trigger current	$V_D=12\text{V}$; $I_T= 0.1\text{A}$, $R_L= 30\ \Omega$	10	mA	
			10		
			10		
			25		
V_{TM}	On-state voltage	$I_T= 15\text{A}$		1.65	V
I_H	Holding current	$I_{GT}= 0.1\text{A}$, $V_D= 12\text{V}$		30	mA
V_{GT}	Gate trigger voltage	$V_D=12\text{V}$; $R_L= 30\ \Omega$ all quadrant		1.5	V